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(71) Applicant: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, P.O. BOX 3453, Sunnyvale, CA 94088-3453 (US).

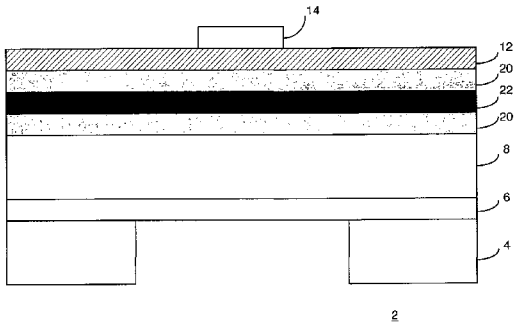
(72) Inventors: **BONSER, Douglas, J.**; 5336 Magdelena Drive, Austin, TX 78735 (US). **PLAT, Marina, V.**; 4620 Corrida Circle, San Jose, CA 95129 (US). **YANG, Chih, Yuh**; 1144 Little John Way, San Jose, CA 95129 (US). **BELL, Scott, A.**; 2313 Stokes Street, San Jose, CA 95128 (US). **CHAN, Darin, A.**; 2054 Anthony Drive, Campbell, CA 95008 (US). **FISHER, Philip, A.**; 730 Chebec Lane, Foster City, CA 94404 (US). **LYONS, Christopher, F.**; 42681 Lerwick Street, Fremont, CA 94539 (US). **CHANG, Mark, S.**; 1881 Famdon Avenue, Los Altos, CA 94024 (US). **GAO, Pei-Yuan**; 1083 Bentoak Lane, San Jose, CA 95129 (US). **WRIGHT, Marilyn, I.**; 712 Glencoe Court, Sunnyvale, CA 94087 (US). **YOU, Lu**; 5978 Friar Way, San Jose, CA 95129 (US). **DAKSHINA-MURTHY, Srikanteswara**; 170 Pasito terrace, Apt. #804, Sunnyvale, CA 94086 (US).

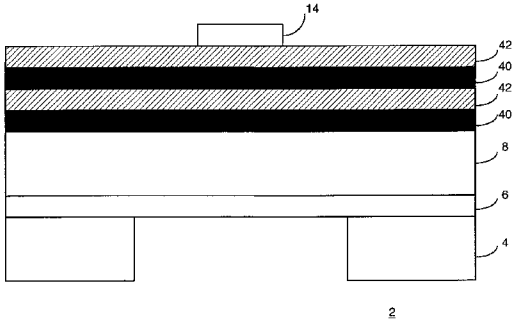
(74) Agent: **COLLOPY, Daniel R.**; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

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(54) Title: METHOD FOR REDUCING PATTERN DEFORMATION AND PHOTORESIST POISONING IN SEMICONDUCTOR DEVICE FABRICATION





(57) Abstract: A hardmask stack is comprised of alternating layers of doped amorphous carbon (22) and undoped amorphous carbon (20). The undoped amorphous carbon layers (20) serve as buffer layers that constrain the effects of compressive stress within the doped amorphous carbon layers (22) to prevent delamination. The stack is provided with a top capping layer (12). The layer beneath the capping layer (12) is preferably undoped amorphous carbon to reduce photoresist poisoning. An alternative hardmask stack is comprised of alternating layers of capping material (42) and amorphous carbon (40). The amorphous carbon layers (40) may be doped or undoped. The capping material layers (42) serve as buffer layers that constrain the effects of compressive stress within the amorphous carbon layers (40) to prevent delamination. The top layer of the stack is formed of a capping material (42). The layer beneath the top layer is preferably undoped amorphous carbon (40) to reduce photoresist poisoning. The lowest layer of the hardmask stack is preferably amorphous carbon (40) to facilitate easy removal of the hardmask stack from underlyingmaterials(8) by an ashing process.

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